9th International Workshop on Characterization and Modeling of Memory devices

September 27th - 28th 2018
University of Milano-Bicocca, Building U6, Room U6-09 (Ground Floor)
Piazza dell’Ateneo Nuovo 1, Milan (Italy)

SCHEDULE

SEPTMBER 27th

9.30 a.m. Registration

10.10 a.m. Welcome
Gianfranco Pacchioni, Pro-Rector for Research, University of Milano-Bicocca

10.20 a.m. 1st Session: Plenary Talks
10.20 a.m. Integrating CMOS and emerging memories for machine learning - Yusuf Leblebici - EPFL, Lausanne - Switzerland
11.05 a.m. Spin-Transfer-Torque MRAM: the Next Revolution in Memory - Daniel C. Worledge - IBM Almaden Research Center - USA
11.50 a.m. Scaling Perspectives of 3D NAND - Akira Goda - Micron Technology, Boise - USA

12.35 a.m. Lunch

2.00 p.m. 2nd Session: Phase Change and Ovonic Materials
2.00 p.m. Ab initio Guided Design of an Ultrafast Phase-Change Material - Riccardo Mazzarello - Aachen University - Germany
2.35 p.m. Exploiting Nanoscale Effects in Phase-Change Memories - Martin Salinaga - Aachen University - Germany
3.10 p.m. Terahertz Studies in Phase Change Materials: Toward Ultrafast Phase Change Operation and Photonics - Kotaro Makino - AIST, Tsukuba - Japan
3.45 p.m. Ovonic Threshold Switching Selector and Non-Volatile Resistive Memory Co-Inegration Towards 3D PCM and RRAM Crossbar Memory Featuring High Density and High Endurance Performance - Gabriele Navarro - CEA, LETI, Grenoble - France

4.20 p.m. Coffee Break

SEPTMBER 28th

9.00 a.m. 3rd Session: Oxide RRAM
9.00 a.m. Cross-layer Design Strategy for Accelerating Deep Learning Using Emerging Resistive Memory Technology - Tuo-Hung Hou - National Chiao Tung University - Taiwan
9.35 a.m. Multiscale Modeling of Novel Memory Devices: Linking Materials to Devices for Accurate Performance and Reliability Predictions - Luca Larcher - University of Modena and Reggio Emilia - Italy
10.10 a.m. Oxide RRAM for Spiking Neural Networks - Sabina Spiga - CNR-IMM, Agrate Brianza - Italy

10.45 a.m. Coffee Break

11.15 a.m. 4th Session: Ferroelectrics and Ferromagnetics
11.15 a.m. A Potential Alternative for DRAM and NAND: Ferroelectric HfO2 Thin Film - Karine Florent - KU Leuven - Belgium
11.50 a.m. Current Status of FeRAM Technologies and Prospects for Beyond Memory Application - Stefan Slesazeck - NaMLab, Dresden - Germany
12.25 a.m. Towards High Density STT-MRAM at sub-20nm Nodes - Bernard Dieny - Université Grenoble Alpes - France

1.00 p.m. Lunch & Adjourn

CLICK HERE TO REGISTER
More info available on the workshop website at www.iwcm2.eu
Fondazione Politecnico di Milano
E. comunicazione@fondazione.polimi.it
Ph. + 39 02 2399 2950